

<b>INFORMATION DISCLOSURE CITATION.</b> (USE SEVERAL SHEETS IF NECESSARY)				ATTY. DOCKET NO. <b>Serie 6550 CIP</b>		SERIAL NO. <b>10/591,629</b>	
				APPLICANT(S) <b>Ashutosh MISRA, et al.</b>			
				FILING DATE <b>09/05/2006</b>		GROUP <b>2818</b>	

  

U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
/A.K./	A1	US 5 470 398	11/28/1995	Shibuya et al.			
/A.K./	A2	US 2004 0198069	10/07/2004	Metzner et al.			
/A.K./	A3	US 2003 111678	6/19/2003	Colombo et al.			
/A.K./	A4	US 2003 207549	11/06/2003	Jenq			
/A.K./	A5	US 6 399 208	6/04/2002	Baum et al.			

  

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/A.K./	C1	International Search Report for PCT/IB2005/000522	
/A.K./	C2	Patent Abstracts of Japan, vol. 2002, no. 06, June 4, 2002 & JP 2002 053960, February 19, 2002	
/A.K./	C3	Ohshita, Y. et al. <i>Hf<sub>1-x</sub>Si<sub>x</sub>O<sub>2</sub> deposition by metal organic chemical vapor deposition using the Hf(NEt<sub>2</sub>)<sub>4</sub>/SiH(NEt<sub>2</sub>)<sub>3</sub>/O<sub>2</sub> gas system</i> , Preparation and Characterization, Elsevier, Sequola, NL, vol. 416, no. 1-2, September 2, 2002, pp. 208-211	
/A.K./	C4	Japan Journal of Applied Physics, vol. 42, no. 6A, pp. L578-L580, June 2003	
/A.K./	C5	Applied Physics Letters, vol. 80, no. 13, pp. 2362-2364, April 2002	

  

Examiner <b>/Arman Khosraviani/</b>	Date Considered <b>09/12/2007</b>
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